Unit: mm

3.0±0.3

23.4

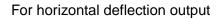
15.5+0.

¢3.2±0.1

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# 2SC5380, 2SC5380A

### Silicon NPN triple diffusion mesa type



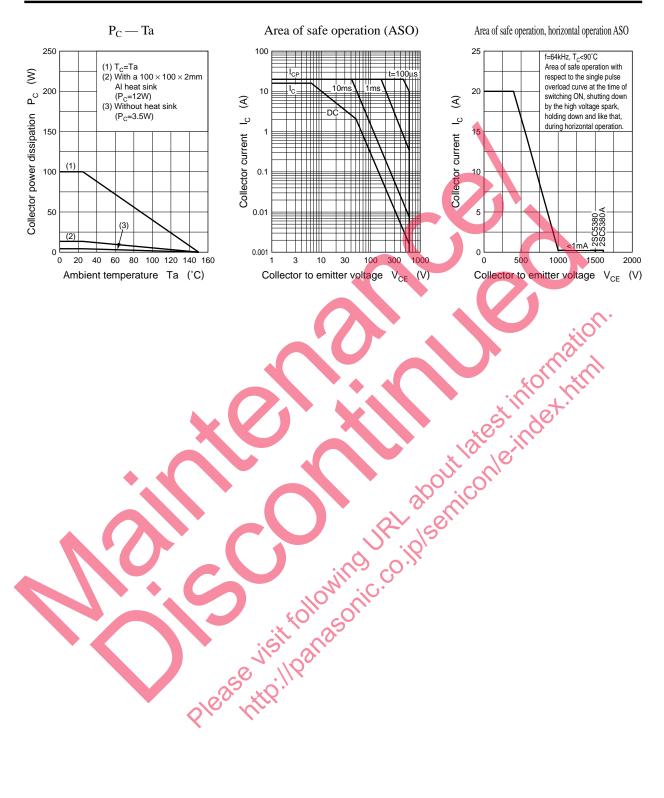
#### Features

- High breakdown voltage, and high reliability through the use of a • glass passivation layer
- High-speed switching
- Wide area of safe operation (ASO) •

Absolute Maximu	m Ratings	$(T_C = 25^{\circ}C)$	
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	1500	V
Collector to emitter voltage	V <sub>CES</sub>	1500	V
	V <sub>CEO</sub>	600	V
Emitter to base voltage	V <sub>EBO</sub>	5	V
Peak collector current	I <sub>CP</sub>	20	A
Collector current	I <sub>C</sub>	16	A
Base current	IB	8	A
Collector power $T_C=25^{\circ}C$	Pc	100	w
dissipation Ta=25°C		3.5	
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C
			ing
Electrical Charac	teristics (T <sub>C</sub>	=25°C)	NN' il

#### Electrical Characteristics (T<sub>c</sub>=25°C)

Parameter	Symbo	I Conditions	min	typ	max	Unit
Collector cutoff 2SC5		$V_{CB} = 1000 V, I_E = 0$			50	μA
current 2SC5	380A	$V_{CB} = 0500$ V, $I_E = 0$			1	mA
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 5V, I_C = 0$			50	μA
Forward current transfer rat	io h <sub>FE</sub>	$V_{CE} = 5V, I_C = 8A$	8		16	
Collector to emitter saturation	voltage V <sub>CE(sat)</sub>	$I_{\rm C} = 8$ A, $I_{\rm B} = 2$ A			3	v
Base to emitter saturation ve	*	$I_{\rm C} = 8$ A, $I_{\rm B} = 2$ A			1.5	v
Transition frequency	f <sub>T</sub>	$V_{CE} = 10V, I_C = 0.1A, f = 0.5MHz$		3		MHz
Storage time	t <sub>stg</sub>				4.0	μs
Fall time	t <sub>f</sub>	$I_{\rm C} = 8A, I_{\rm B1} = 2A, I_{\rm B2} = -4A$			0.3	μs



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